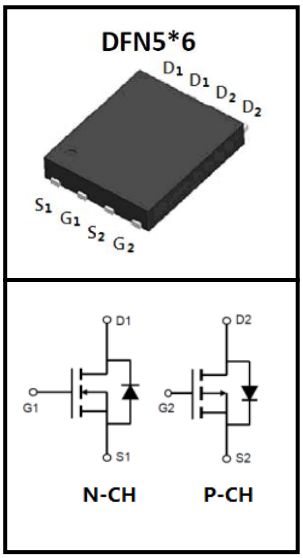
N+P-Channel Logic Level Enhancement Mode Power MOSFET

FEATURES

- Super Low Gate Charge
- 100% EAS Guaranteed
- RoHS compliant
- Green Device Available
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology



APPLICATIONS

- H-bridge
- Inverters

RoHS

Device Marking and Package Information

Device	Package	Marking
CTN04PN035	DFN5*6	CTN04PN035

Absolute Maximum Ratings at T_j= 25ºC unless otherwise noted

Parameter	Symbol	Value		Unit
Drain-Source Voltage (V_{GS} = 0V)	V_{DSS}	40	-40	V
Continuous Drain Current T_C = 25ºC (note1)	I_D	18	-18	A
Continuous Drain Current T_C = 100ºC (note1)		10	-9.5	
Pulsed Drain Current (note2)	I_{DM}	32	-26	A
Gate Source Voltage	V_{GSS}	±20	±20	V
Power Dissipation T_C = 25ºC (note4)	P_D	10	20	W
Single Pulse Avalanche Energy (note3)	E_{AS}	12	25	mJ
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+175		ºC

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance,Junction-to-Case	$R_{\theta JC}$	40	℃/W
Thermal Resistance,Junction-to-Ambient	$R_{\theta JA}$	65	℃/W

Electrical Characteristics T_j= 25ºC unless otherwise specified						
Parameter	**Symbol**	**Test Conditions**	**Value**			**Unit**
			Min.	**Typ.**	**Max.**	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	40	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 32V, V_{GS} = 0V, T_J = 25ºC	--	--	1	uA
		V_{DS} = 32V, V_{GS} = 0V, T_J = 100ºC	--	--	5	uA
Gate-Source Leakage	I_{GSS}	V_{GS} = ±20V	--	--	±100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1.2	--	2.5	V
Drain-Source On-Resistance (note2)	$R_{DS(on)}$	V_{GS} = 10V, I_D = 15A	--	15	20	mΩ
		V_{GS} = 4.5V, I_D = 10A	--	17	23	mΩ
Dynamic						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 15V, f = 1.0MHz	--	415	--	pF
Output Capacitance	C_{oss}		--	112	--	
Reverse Transfer Capacitance	C_{rss}		--	11	--	
Total Gate Charge （4.5V）	Q_g	V_{DS} = 30V, I_D = 4A, V_{GS} = 10V	--	6.5	--	nC
Gate-Source Charge	Q_{gs}		--	1.2	--	
Gate-Drain Charge	Q_{gd}		--	1.1	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DS} = 15V, I_D = 4A V_{GS} = 10V,R_G = 3.3Ω	--	4	--	ns
Turn-on Rise Time	t_r		--	3	--	
Turn-off Delay Time	$t_{d(off)}$		--	15	--	
Turn-off Fall Time	t_f		--	2	--	
Body Diode Characteristics						
Continuous Body Diode Current	I_S		--	--	18	A
Pulsed Diode Forward Current	I_{SM}		--	--	32	A
Body Diode Voltage	V_{SD}	I_{SD} = 1A, V_{GS} = 0V	--	--	1.2	V

Notes

1. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.
2. The data tested by pulsed , pulse width≦300us , duty cycle≦2%
3. The EAS data shows Max. rating . The test condition is VDD =25V,VGS =10V,L=0.1mH
4. The power dissipation is limited by 175℃ junction temperature
5. The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Electrical Characteristics T_j= 25ºC unless otherwise specified						
Parameter	**Symbol**	**Test Conditions**	**Value**			**Unit**
			Min.	**Typ.**	**Max.**	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	-40	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -32V, V_{GS} = 0V, T_J = 25ºC	--	--	1	uA
		V_{DS} = -32V, V_{GS} = 0V, T_J = 100ºC	--	--	5	uA
Gate-Source Leakage	I_{GSS}	V_{GS} = ±20V	--	--	±100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250μA	-1.2	--	-2.5	V
Drain-Source On-Resistance (note2)	$R_{DS(on)}$	V_{GS} = -10V, I_D = -15A	--	29	35	mΩ
		V_{GS} = -4.5V, I_D = -10A	--	38.5	46	mΩ
Dynamic						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = -15V, f = 1.0MHz	--	1040	--	pF
Output Capacitance	C_{oss}		--	180	--	
Reverse Transfer Capacitance	C_{rss}		--	125	--	
Total Gate Charge （4.5V）	Q_g	V_{DS} = -30V, I_D = -4A, V_{GS} = -10V	--	19	--	nC
Gate-Source Charge	Q_{gs}		--	3.6	--	
Gate-Drain Charge	Q_{gd}		--	4.6	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DS} = -15V, I_D = -4A V_{GS} = -10V,R_G = 3.3Ω	--	10	--	ns
Turn-on Rise Time	t_r		--	5.5	--	
Turn-off Delay Time	$t_{d(off)}$		--	3.6	--	
Turn-off Fall Time	t_f		--	4.6	--	
Body Diode Characteristics						
Continuous Body Diode Current	I_S		--	--	-18	A
Pulsed Diode Forward Current	I_{SM}		--	--	-26	A
Body Diode Voltage	V_{SD}	I_{SD} = -1A, V_{GS} = 0V	--	--	-1.2	V

Notes

1. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.
2. The data tested by pulsed , pulse width≦300us , duty cycle≦2%
3. The EAS data shows Max. rating . The test condition is VDD =25V,VGS =10V,L=0.1mH
4. The power dissipation is limited by 175℃ junction temperature
5. The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Figure A：Gate Charge Test Circuit and Waveform

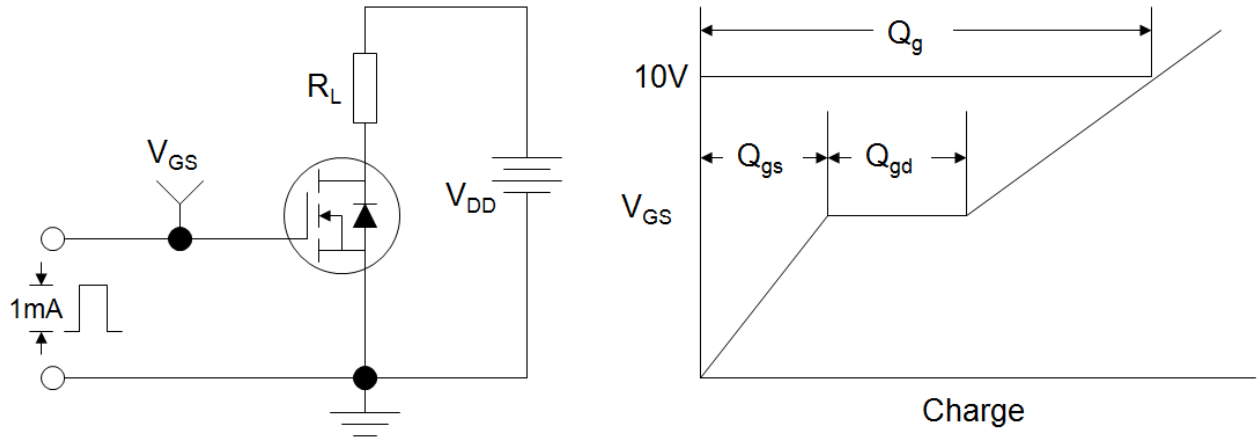


Figure B：Resistive Switching Test Circuit and Waveform

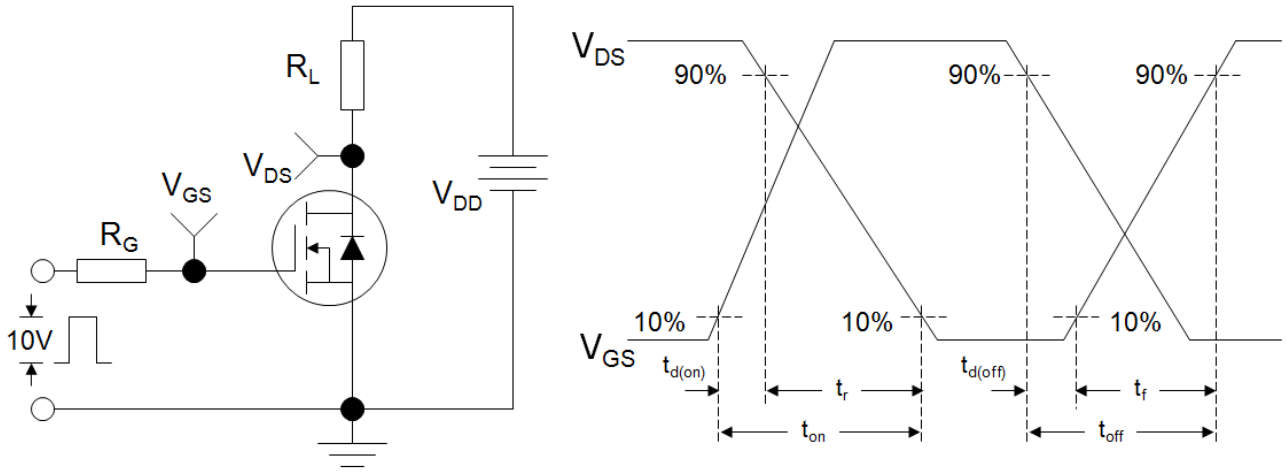
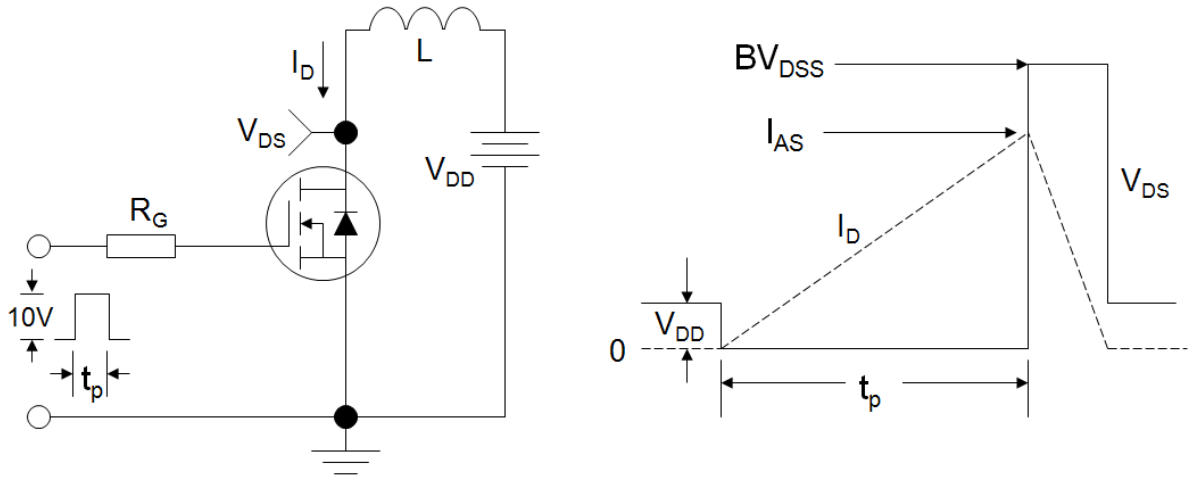


Figure C：Unclamped Inductive Switching Test Circuit and Waveform



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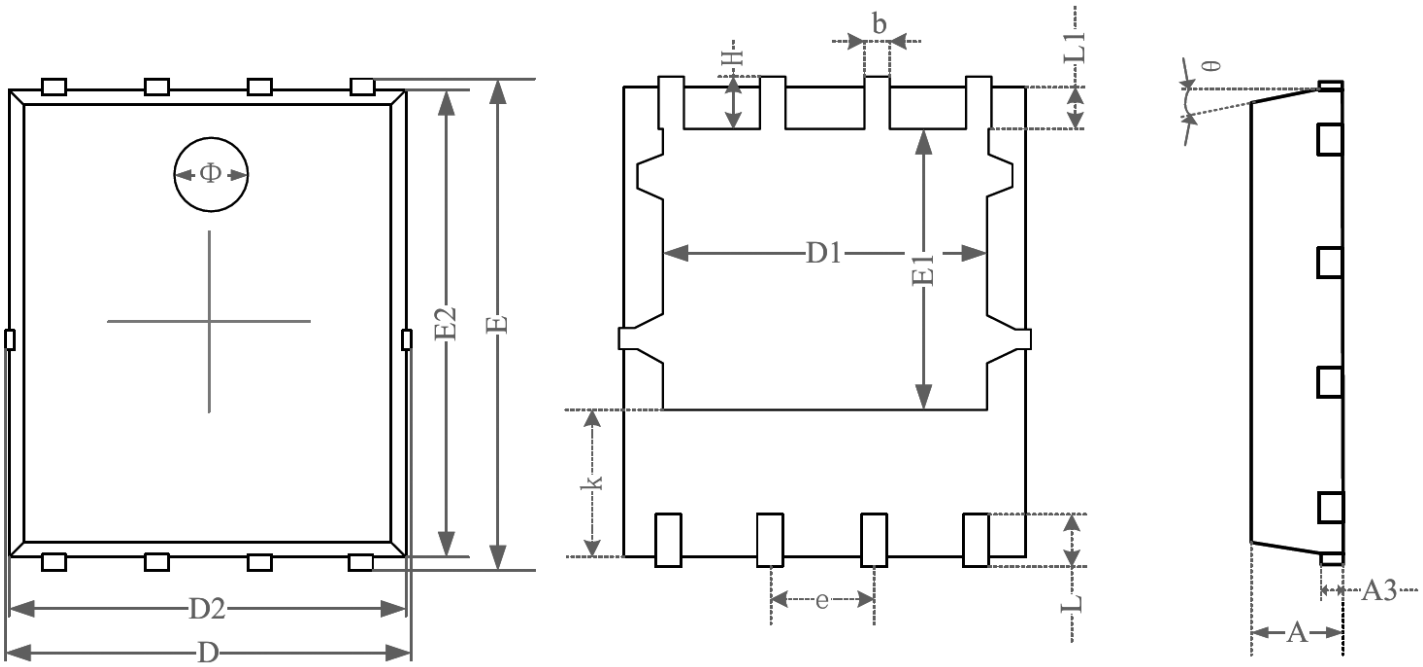

SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.870	0.900	0.930	0.034	0.035	0.036
A3	0.152REF.			0.006REF.		
D	4.944	5.020	5.096	0.195	0.198	0.201
E	5.974	6.050	6.126	0.235	0.238	0.241
D1	3.910	4.010	4.110	0.154	0.158	0.162
E1	3.375	3.475	3.575	0.133	0.137	0.141
D2	4.870	4.900	4.930	0.192	0.193	0.194
E2	5.720	5.750	5.780	0.226	0.227	0.228
k	1.190	1.290	1.390	0.047	0.051	0.055
b	0.350	0.380	0.410	0.014	0.015	0.016
e	1.270TYP.			0.050TYP.		
L	0.559	0.635	0.711	0.022	0.025	0.028
L1	0.424	0.500	0.576	0.017	0.020	0.023
H	0.574	0.650	0.726	0.023	0.026	0.029
θ	10°	11°	12°	10°	11°	12°
Φ	1.150	1.200	1.250	0.045	0.047	0.049

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